




*EE141-Fall 2012  
Digital Integrated  
Circuits*

Lecture 13  
CMOS Logic Review

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*CMOS Logic  
Review*

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*Announcements*

- Midterm tonight 6:30pm sharp
- Homework #6 out tonight, due next Thurs.
- Reminder:
  - Project coming up in 2 weeks – find a partner

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*Cell Design*

- Standard Cells
  - General purpose logic
  - Used to synthesize RTL/HDL
  - Same height, varying width
- Datapath Cells
  - For regular, structured designs (arithmetic)
  - Includes some wiring in the cell

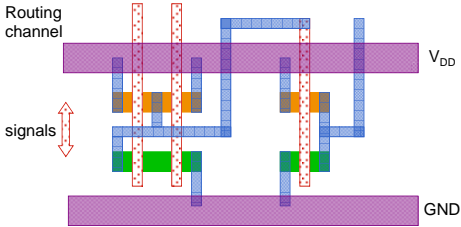
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*Class Material*

- Last lecture
  - CMOS Delay and Power Models
- Today's lecture
  - CMOS Logic Review
- Reading (6)

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*Standard Cell Layout Methodology –  
1980s*



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### Standard Cell Layout Methodology - 1990s - Today

Mirrored Cell

No routing channels

$V_{DD}$

$V_{DD}$

M2

M3

GND

GND

Mirrored Cell

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### Stick Diagrams

Contains no dimensions  
Represents relative positions of transistors

Inverter

$V_{DD}$

GND

In

Out

NAND2

$V_{DD}$

GND

A

B

Out

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### Standard Cells

N Well

$V_{DD}$

Cell height 12 metal tracks  
Metal track is approx.  $3\lambda + 3\lambda$   
Pitch = repetitive distance between objects  
Cell height is "12 Mn pitch"

$2\lambda$

In

Out

GND

Cell boundary

Rails  $\sim 10\lambda$

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### Stick Diagrams

How to lay this gate out to minimize area?

A

B

C

F

C

$X = C \cdot (A + B)$

A

B

C

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### Standard Cells

With minimal diffusion routing

$V_{DD}$

$V_{DD}$

In

Out

GND

GND

With silicided diffusion

$V_{DD}$

$V_{DD}$

In

Out

GND

GND

$V_{DD}$

In

Out

GND

GND

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### Two Versions of $C \cdot (A + B)$

A

C

B

$V_{DD}$

GND

X

A

B

C

$V_{DD}$

GND

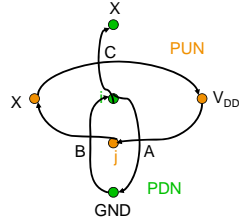
X

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### Consistent Euler Path

A B C  
Has PDN and PUP

B C A  
Has PUP, but no PDN

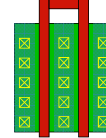


### Multi-Fingered Transistors

How can you fit wide transistors into a fixed height?

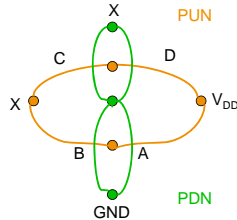
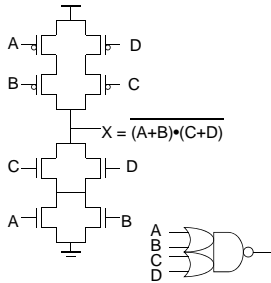
One finger

Two fingers (folded)



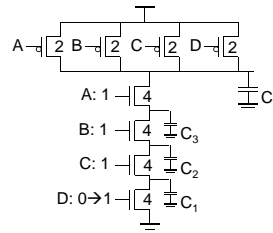
Less diffusion capacitance

### OAI22 Logic Graph

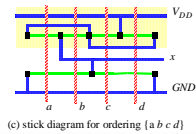
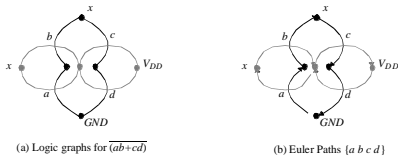


### Fan-In Considerations

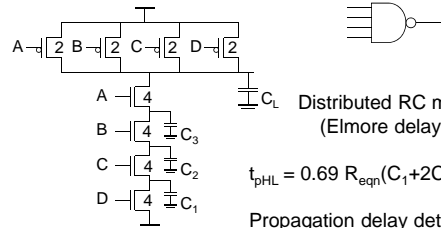
RC model:



### Example: $x = ab+cd$



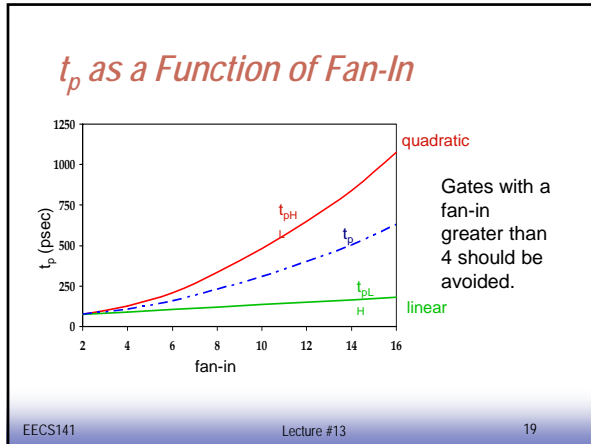
### Fan-In Considerations



Distributed RC model (Elmore delay)

$$t_{pHL} = 0.69 R_{eqn}(C_1+2C_2+3C_3+4C_L)$$

Propagation delay deteriorates rapidly as a function of fan-in – quadratically in the worst case.

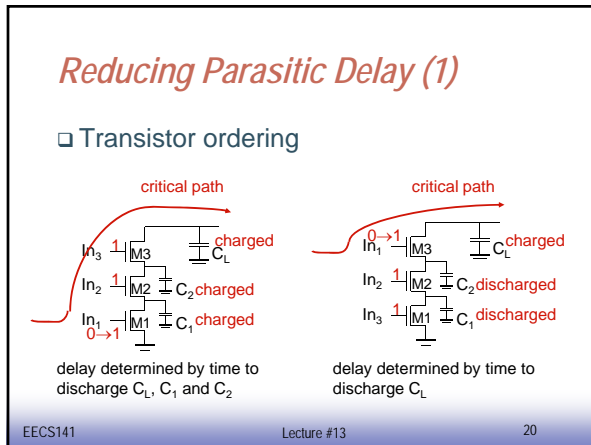


### Reducing Delay (3)

- Reducing the voltage swing
 
$$t_{pHL} = 0.5 (C_L V_{DD}) / I_{DSATn}$$

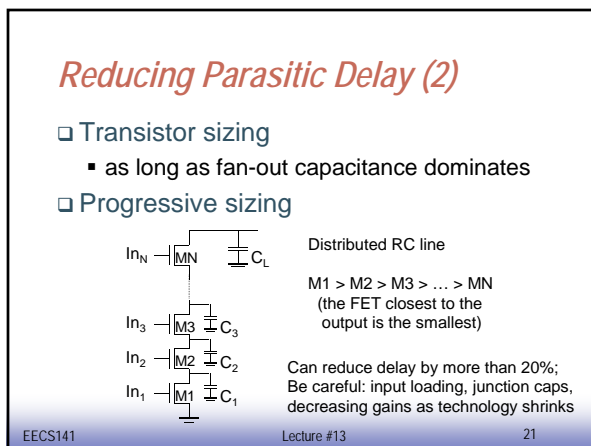
$$= 0.5 (C_L V_{swing}) / I_{DSATn}$$
  - linear reduction in delay
  - also reduces power consumption
- But the following gate is slower!
- Or requires use of “sense amplifiers” on the receiving end to restore the signal level (memory design)

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### LE in Modern Processes

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### LE in Modern Processes

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*Next Lecture*

- Wires